

GSDSB5819W

Schottky Barrier Rectifier

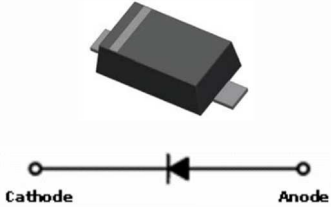
Product Description

Schottky Barrier Diodes 500mW / 40V

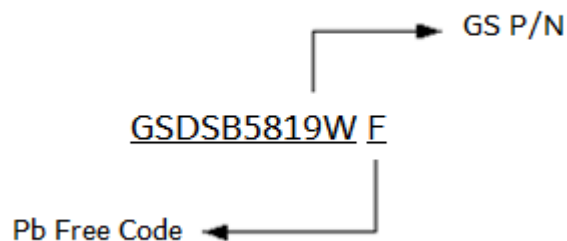
Features

- For use in low voltage, high frequency inverters, free wheeling & polarity protection
- Flat Lead SOD-123 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode
- Weight: approx.0.01g

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit Diagram
GSDSB5819WF	SOD-123	SL	

Ordering Information



Part Number	Package	Quantity
GSDSB5819WF	SOD-123	3,000 PCS

Absolute Maximum Ratings

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	500	mW
V _{RM}	Repetitive Peak Reverse Voltage	40	V
T _J	Operating Junction Temperature	150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C
I _O	Average Rectified Output Current	1	A
I _{FSM}	Forward current surge peak (t=8.3ms Single Half Sine-wave)	9	A
I _{FRM}	Repetitive Peak Forward Current	1.5	A

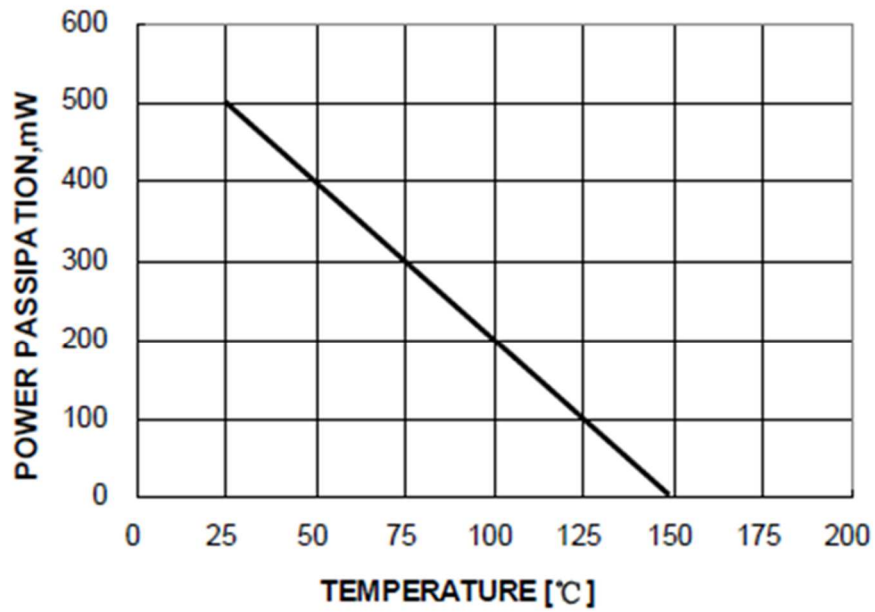
These ratings are limiting values above which the serviceability of the diode may be impaired.

Electrical Characteristics

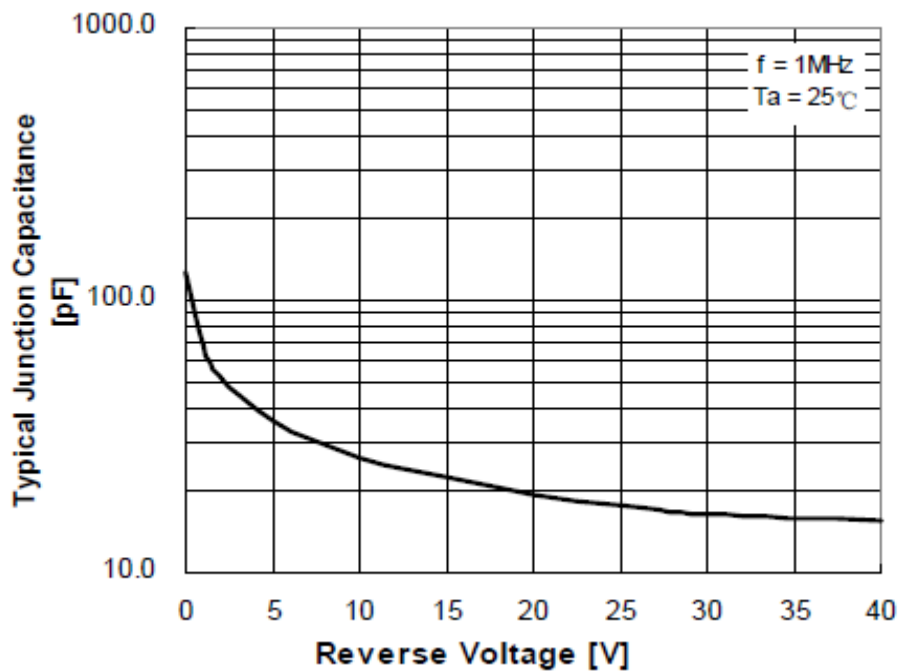
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _{BR}	Reverse Breakdown Voltage	I _R =1mA	40			V
I _R	Reverse Leakage Current	V _R =40V	-	-	1	mA
V _F	Forward Voltage	I _F =1A I _F =3A	-	-	0.60 0.90	V
C _d	Diode Capacitance	V _R =4V f=1MHZ			120	pF

Typical Characteristics

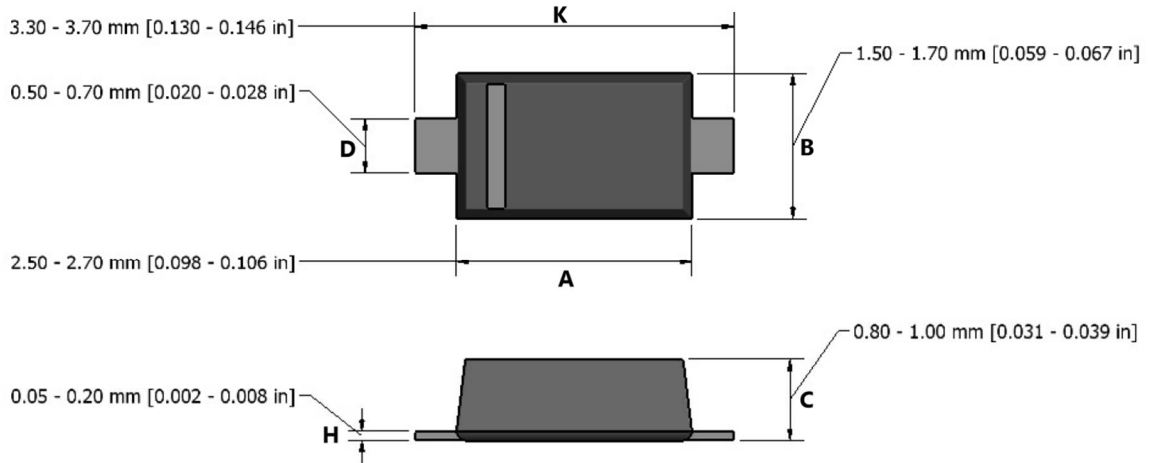


POWER DISSIPATION VS. AMBIENT TEMP.



Package Dimension

SOD-123



Note: Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.





Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.5	2.7	0.098	0.106
B	1.5	1.7	0.059	0.067
C	0.8	1	0.031	0.039
D	0.5	0.7	0.02	0.028
H	0.05	0.2	0.002	0.008
K	3.3	3.7	0.13	0.146

NOTICE

Information furnished is believed to be accurate and reliable. However Globaltech Semiconductor assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties, which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Globaltech Semiconductor. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information without express written approval of Globaltech Semiconductor.

CONTACT US

GS Headquarter

	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

RD Division

	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587